

Abstracts

High-voltage GaAs power-HBTs for base-station amplifiers

P. Kurpas, F. Brunner, R. Doemer, B. Janke, P. Heymann, A. Maasdorf, W. Doser, P. Auxemery, H. Blanck, D. Pons, J. Wurfl and W. Heinrich. "High-voltage GaAs power-HBTs for base-station amplifiers." 2001 MTT-S International Microwave Symposium Digest 01.2 (2001 Vol. II [MWSYM]): 633-636 vol.2.

Base stations require high-power devices operating at bias voltages around 26 V. This paper reports on GaAs HBTs with increased breakdown voltage. Transistors on unthinned wafers deliver 3.2 W at 2 GHz for 27 V bias. 100 Ohms output impedance and 74% PAE make them very attractive for base-station amplifiers.

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